

## **NCE P-Channel Super Trench Power MOSFET**

### **Description**

The NCEP40P80D uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{\text{DS(ON)}}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### **General Features**

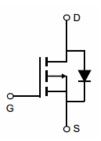
•  $V_{DS}$  =-40V, $I_{D}$  =-80A  $R_{DS(ON)}$ =5.6mΩ (typical) @  $V_{GS}$ =-10V  $R_{DS(ON)}$ =7.6mΩ (typical) @  $V_{GS}$ =-4.5V

- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

# **Application**

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED! 100% ΔVds TESTED!



Schematic Diagram



Marking and pin assignment



TO-263-2L top view

### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP40P80D	NCEP40P80D	TO-263-2L	-	-	-

### Absolute Maximum Ratings (T<sub>C</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	-40	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	I <sub>D</sub>	-80	Α
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100℃)	-56.5	Α
Pulsed Drain Current	I <sub>DM</sub>	-320	Α
Maximum Power Dissipation	P <sub>D</sub>	150	W
Derating factor		1	<b>W</b> /℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	500	mJ
Operating Junction and Storage Temperature Range	$T_{J}$ , $T_{STG}$	-55 To 175	$^{\circ}$ C



# http://www.ncepower.com

# NCEP40P80D

## **Thermal Characteristic**

Thermal Resistance, Junction-to-Case (Note 2)	R <sub>eJC</sub>	1.0	°C/W	1
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Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

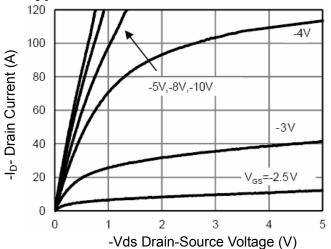
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-40		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-40V,V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)			•			•
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=-250\mu A$	-0.8	-1.2	-1.8	V
Dunin Course On Ctate Desigtance		V <sub>GS</sub> =-10V, I <sub>D</sub> =-40A	-	5.6	6.2	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-40A	-	7.6	9.1	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =-5V,I <sub>D</sub> =-40A	-	30	-	S
Dynamic Characteristics (Note4)			•			•
Input Capacitance	C <sub>Iss</sub>	V <sub>DS</sub> =-20V,V <sub>GS</sub> =0V,	-	3738	-	PF
Output Capacitance	Coss		-	882	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	22	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	10.5	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =-20 $V$ , $I_{D}$ =-40 $A$	-	4	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =-10 $V$ , $R_G$ =1.6 $\Omega$	-	35	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	5	-	nS
Total Gate Charge	Qg	\/ - 20\/ I - 40A	-	57.2	-	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =-20V, $I_{D}$ =-40A,	-	9.8		nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =-10V	-	7.3		nC
Drain-Source Diode Characteristics	·					
Diode Forward Voltage (Note 3)	$V_{SD}$	V <sub>GS</sub> =0V,I <sub>S</sub> =-40A	-		-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-80	Α
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> =-40A	-		24	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-		68	nC

### Notes:

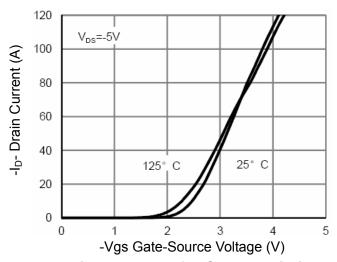
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^{\circ}\!\!\mathrm{C}$  ,V\_DD=-20V,V\_G=-10V,L=0.5mH,Rg=25  $\!\Omega$



## **Typical Electrical and Thermal Characteristics**



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

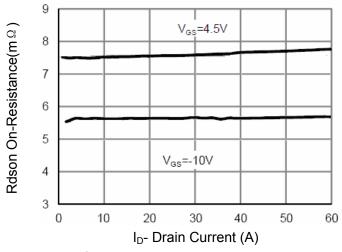


Figure 3 Rdson- Drain Current

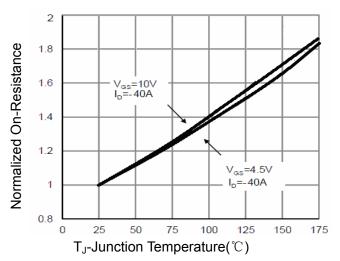


Figure 4 Rdson-JunctionTemperature

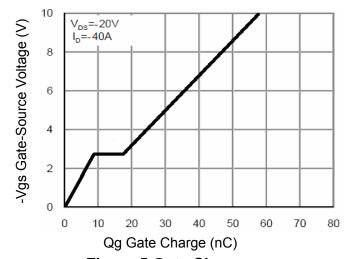


Figure 5 Gate Charge

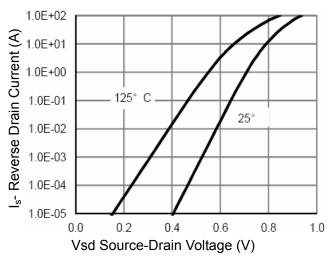


Figure 6 Source- Drain Diode Forward



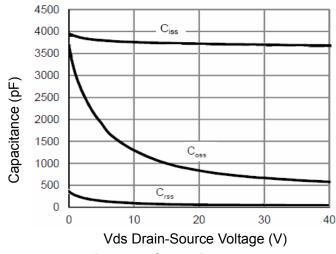


Figure 7 Capacitance vs Vds

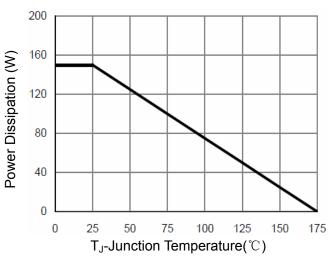
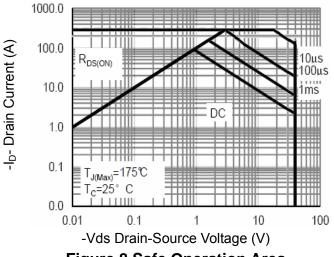


Figure 9 Power De-rating



**Figure 8 Safe Operation Area** 

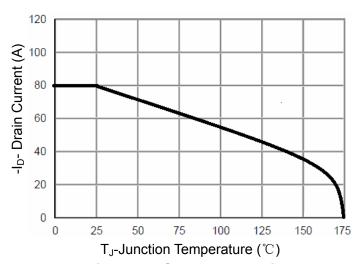
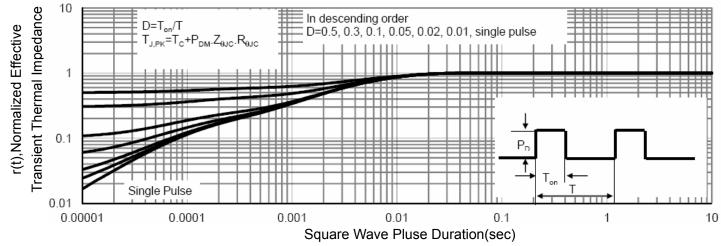


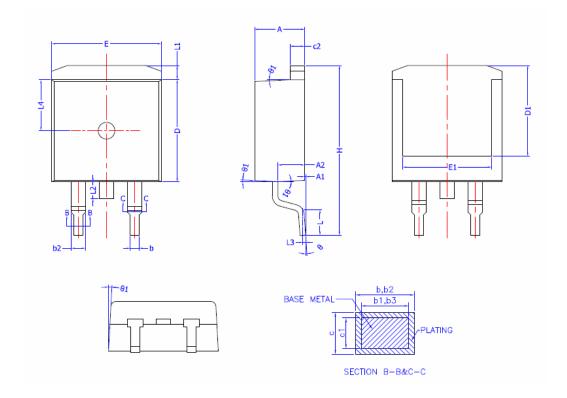
Figure 10 Current De-rating



**Figure 11 Normalized Maximum Transient Thermal Impedance** 



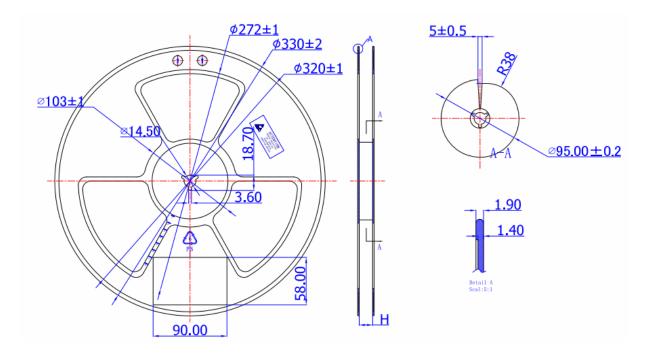
# **TO-263-2L Package Information**

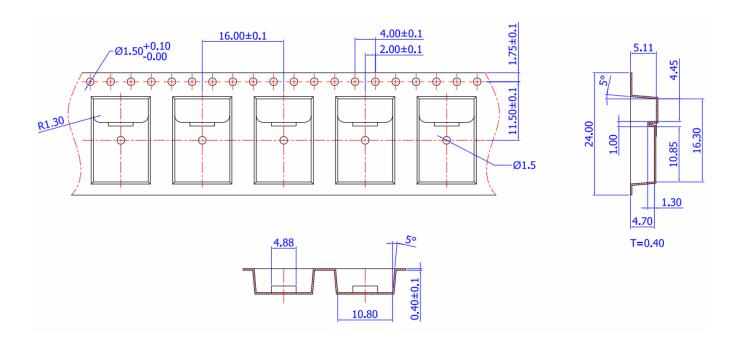


COMMON DIMENSIONS (UNITS OF MEASURE =MILLIMETER)

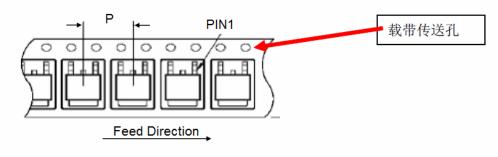
SYMBOL	MIN	NOM	MAX	
Α	4.40	4.50	4.60	
A1	0	0.10	0.25	
A2	2,20	2,40	2,60	
b	0,76	_	0,89	
b1	0,75	0,80	0,85	
b2	1,23		1,37	
b3	1,22	1,27	1,32	
С	0,47	_	0,60	
c1	0.46	0.51	0.56	
c2	1,25	1.30	1.35	
D	9,10	9.20	9.30	
D1	8,00	_	—	
E	9,80	9.90	10.00	
E1	7.80	_	_	
e	2.54 BSC			
Н	14.90	15.30	15.70	
L	2.00	2,30	2.60	
L1	1.17	1.27	1.40	
L2	_	— <b>1.</b> 75		
L3	0.25BSC			
L4	4.60 REF			
θ	0°	— 8°		
θ1	1°	3°	5°	





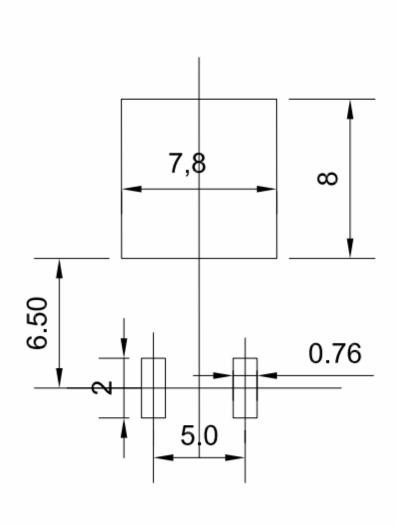


注:产品编入卷盘中时,产品第一支脚(PIN 1)方向朝向载带传送孔。如下图所示。





焊盘





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